



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Fabrice LETERTRE

Confirmation No.: 6657

Application No.: 10/716,451

Group Art Unit: 1765

Filing Date: November 20, 2003

Examiner:

For: METHOD OF FABRICATING
MONOCRYSTALLINE CRYSTALS

Attorney Docket No.: 4717-11500

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed is a Form PTO-1449 listing eleven (11) references for the Examiner's review. The references were cited in the Search Report for the corresponding French application, and a copy of the Search Report is enclosed.

Copies of non-U.S. patent references B1-B6 and C1-C5 are enclosed herewith. Copies of U.S. patent references A1-A3 will be provided if the Examiner so requests.

It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

This Information Disclosure Statement is filed under § 37 CFR 1.97(b)(3), before the mailing of a first Office Action on the merits. Thus, no fee is believed to be due. Should a fee be required, however, please charge such fee to Winston & Strawn LLP Deposit Account No. 50-1814.

Respectfully submitted,

April 26, 2004
Date

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202-371-5904

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|---|-------------|---|---------|--|-------|---------------------------------------|-------------------------------|
| LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 <i>(Use several sheets if necessary)</i> | | | | ATTY. DOCKET NO.: 4717-11500 | | APPLICATION NO.: 10/716,451 | |
| | | | | APPLICANT: Fabrice LETERTRE | | | |
| | | | | FILING DATE: November 20, 2003 | | GROUP: 1765 | |
| U.S. PATENT DOCUMENTS | | | | | | | |
| *EXAMINER INITIAL | CITE NO. | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
| | A1 | 6,328,796 B1 | 12/2001 | Kub et al. | 117 | 94 | |
| | A2 | 2002/0096106 | 07/2002 | Kub et al. | 117 | 94 | |
| | A3 | 2003/0036247 | 02/2003 | Eriksen et al. | 438 | 455 | |
| FOREIGN PATENT DOCUMENTS | | | | | | | |
| | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION YES NO |
| | B1 | WO 96/41906 | 12/1996 | PCT | | | |
| | B2 | EP 0 961 312 | 01/1999 | EPO | | | |
| | B3 | WO 01/68957 | 09/2001 | PCT | | | |
| | B4 | JP 2001 253799 | 09/2001 | Japan (with English abstract) | | | X |
| | B5 | EP 1 245 702 | 02/2002 | EPO | | | |
| | B6 | JP 2003 183097 | 07/2003 | Japan (with English abstract) | | | X |
| OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.) | | | | | | | |
| | C1 | Hugonnard-Bruyère, E., et al., "Deep Level Defectss in H ⁺ Implanted 6H-SiC Epilayers and in Silicon Carbide on Insulator Structures", <i>Materials Science and Engineering B</i> , Vol. 61-62, pp. 382-388 (1999) | | | | | |
| | C2 | Hugonnard-Bruyère, E., et al., "Defect Studies in Epitaxial SiC-6H Layers on Insulator (SiCOI)", <i>Microelectronic Engineering</i> , Vol. 48, pp. 277-280 (1999) | | | | | |
| | C3 | Müller, S.G, et al., "Progress in the Industrial Production of SiC Substrates for Semiconductor Devices", <i>Materials and Science Engineering B</i> , Vol. 80, No. 1-3, pp. 327-331 (2001) | | | | | |
| | C4 | Tsvetkov, V. et al., "SiC Seeded Boule Growth", <i>Materials Science Forum</i> , Vols. 264-268, pp. 3-8 (1998) | | | | | |
| | C5 | Tsvetkov, V.F. et al., "Recent Progress in SiC Crystal Growth", <i>Inst. Phys. Conf. Ser.</i> , No. 142, Chap. 1, pp. 17-22 (1996) | | | | | |
| EXAMINER | | | | DATE CONSIDERED | | | |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | |